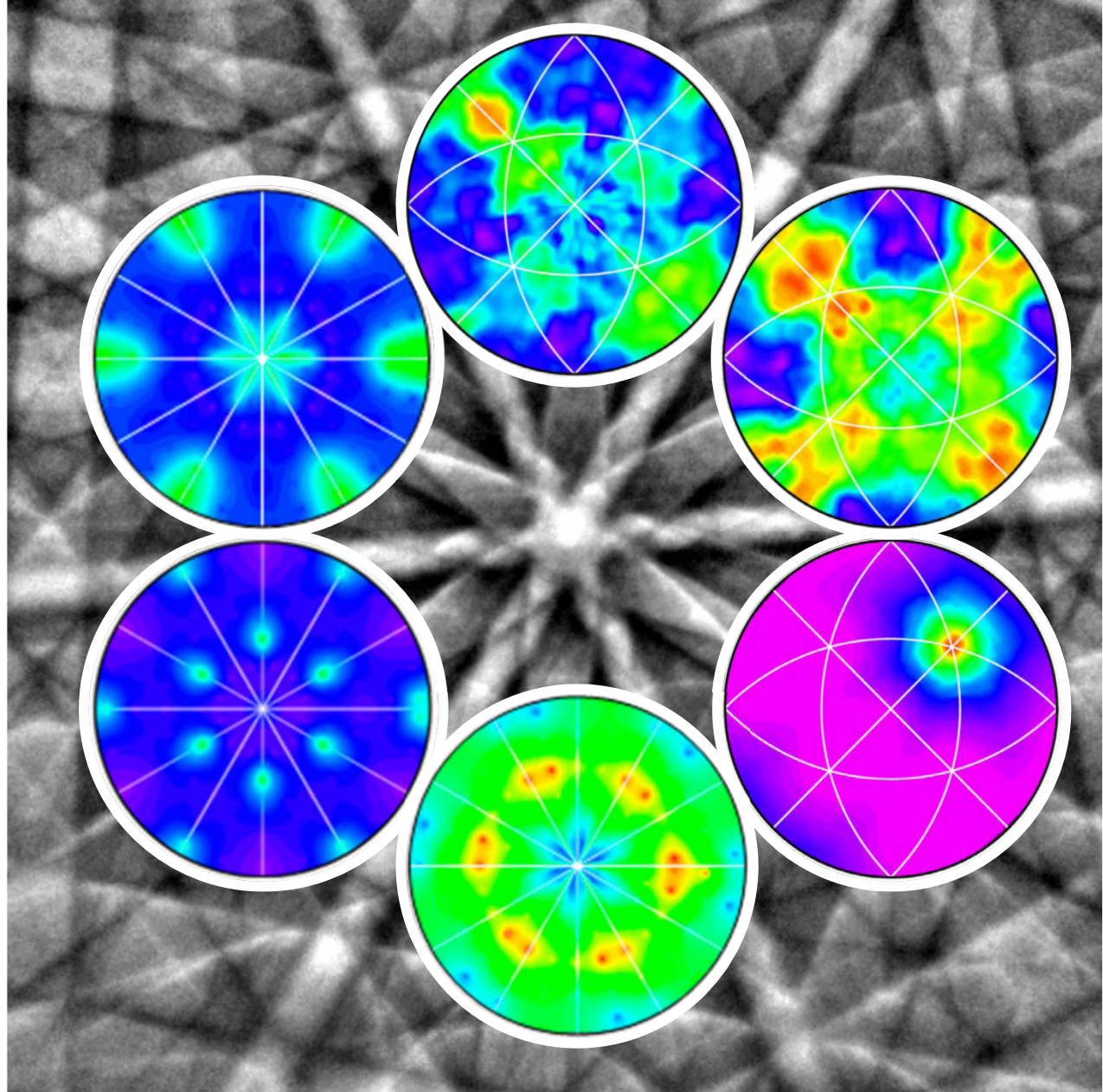


Advanced Ceramic Technologies

Grain boundaries: complexions and character



Outline

*What's on the
- MENU -
today ?*

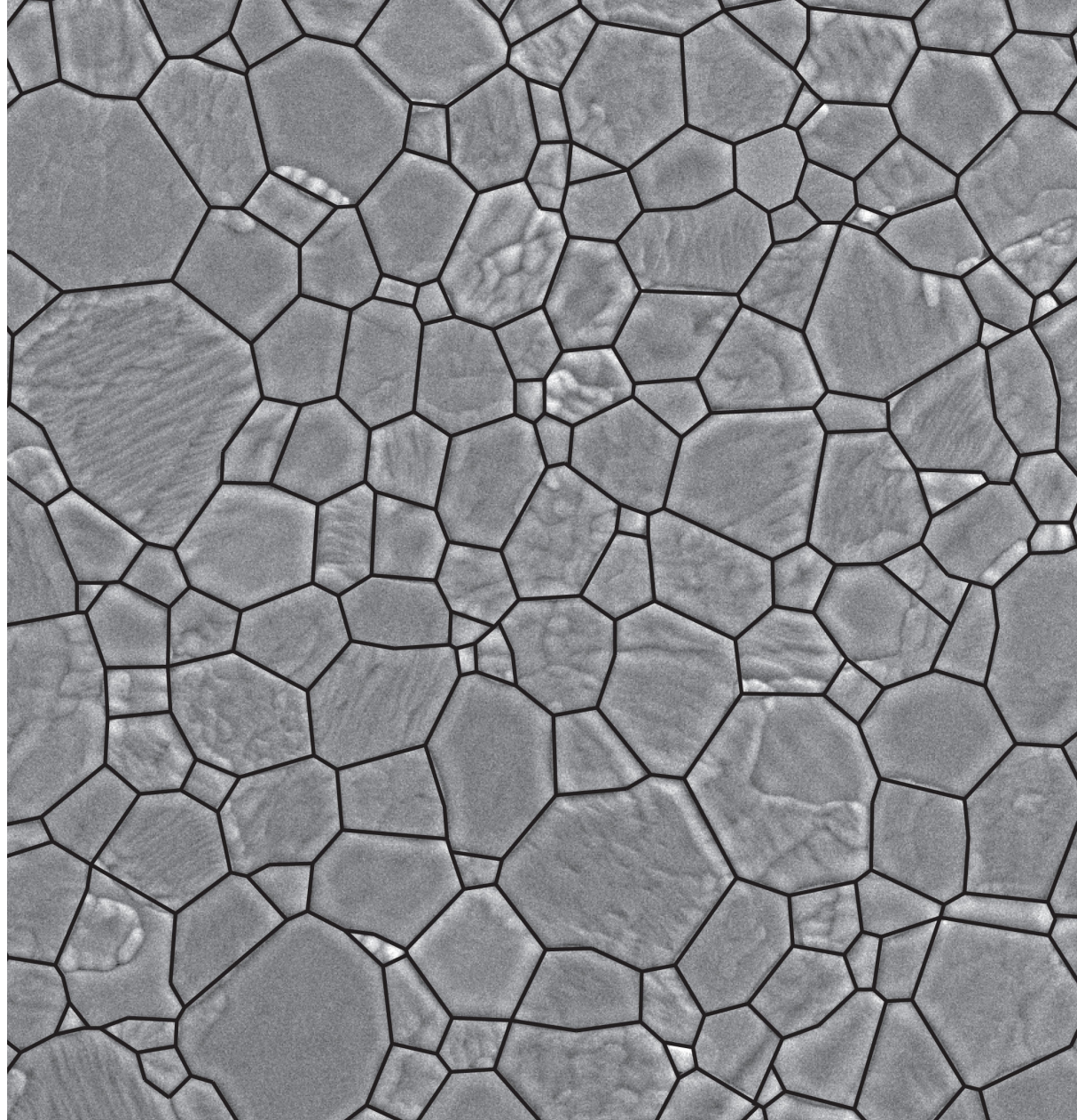


- ◆ Complexions and complexion transitions
 - Thermodynamic description
 - Role of grain boundary energy and grain growth
- ◆ EBSD basics
 - Stereographic projections, pole figures and inverse pole figures
- ◆ Stereological EBSD analysis
 - Description of stereological method
- ◆ Effect of complexion transitions on grain boundary plane/character distribution

Learning objectives:

- ◆ Understand the complexity behind grain boundary engineering (5-geometric, complexions, ...)
- ◆ Acquire method to investigate grain boundary character distribution in microstructures
- ◆ Illustrate direct consequences of complexion transitions

**(simplified)
Grain boundary
descriptors**



Grain boundary description methods

♦ **Geometric** (and structural) description

- **Twist:** one part of crystal rotated around an axis normal to the boundary plane
- **Tilt:** one part of crystal twisted around an axis in the boundary plane

♦ **Misorientation angle** based description

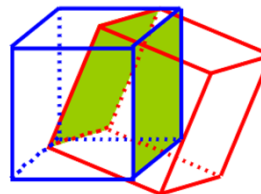
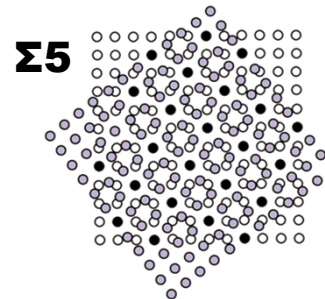
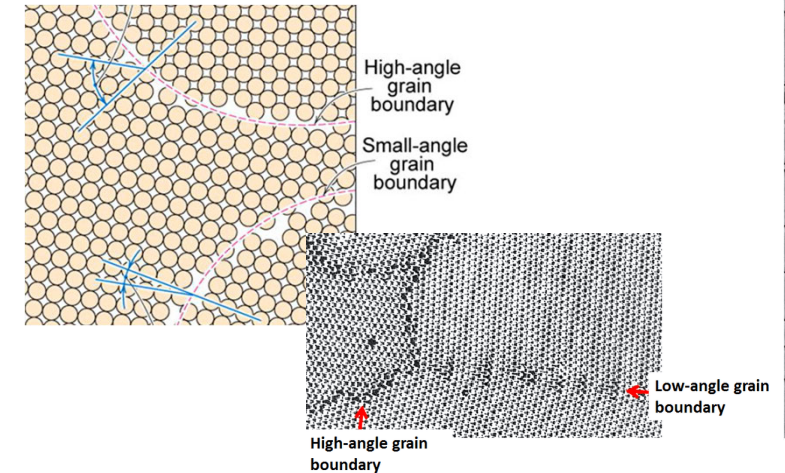
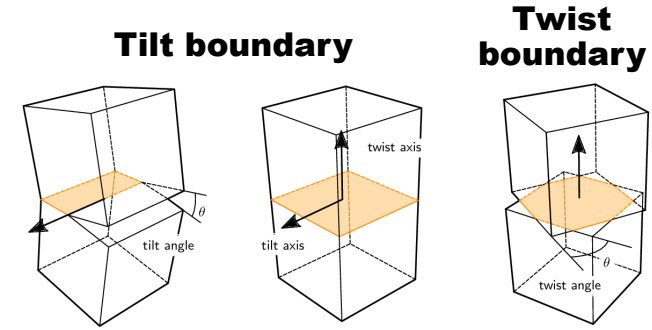
- Low angle: misorientation $< 15^\circ$ (typically lower energies)
- High angle: misorientation $> 15^\circ$ (typically higher energies)

♦ **Coincidence site lattice (CSL)** boundaries

- Describes degree of lattice matching between two grains
- Lower Σ values indicate higher atomic coincidence and lower boundary energy (e.g. $\Sigma 3$ for twin boundaries)

♦ **Crystallographic** description

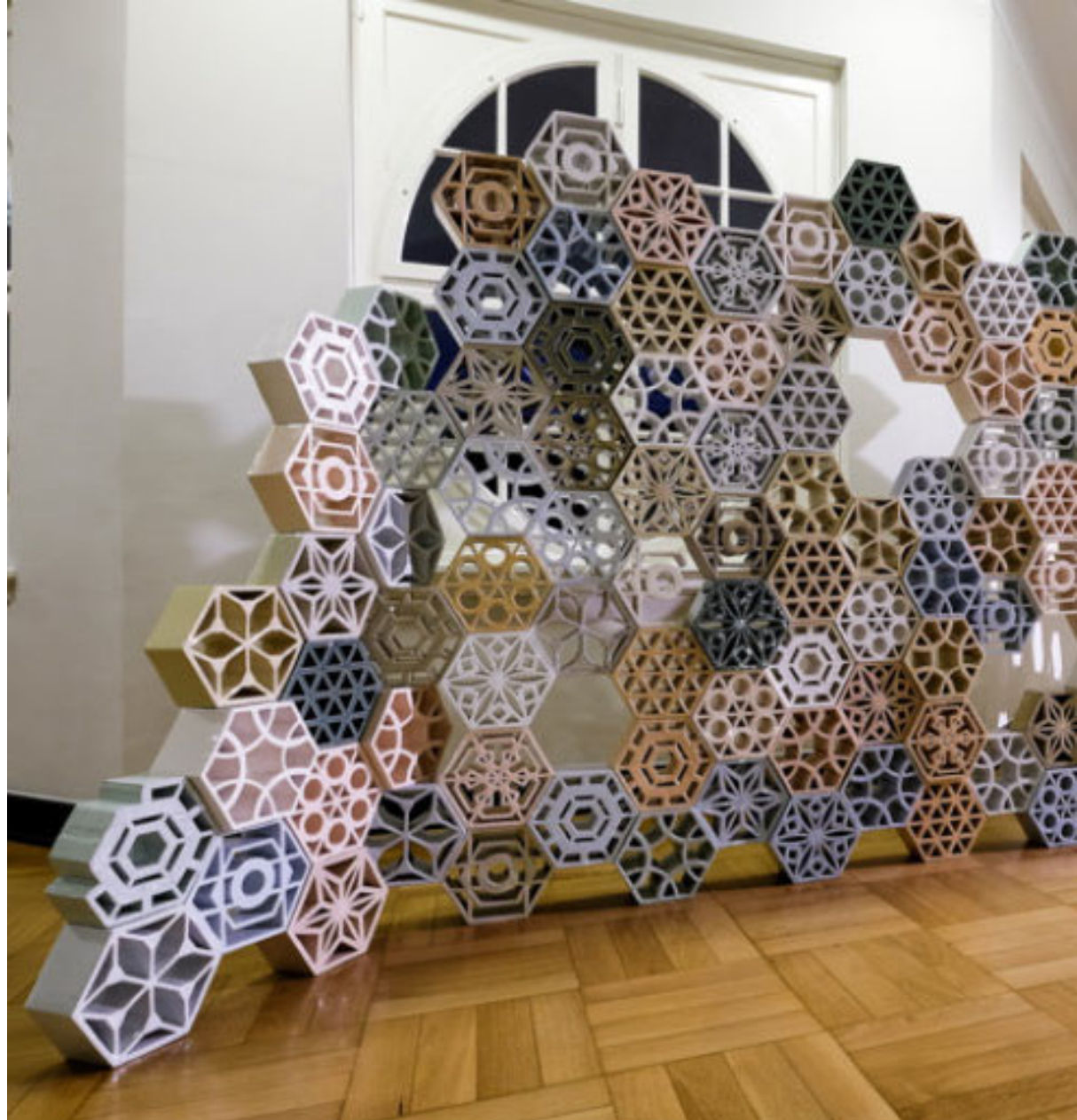
- Based on 5 macroscopic parameters
 - Lattice misorientation + Boundary plane normal



Important to note:

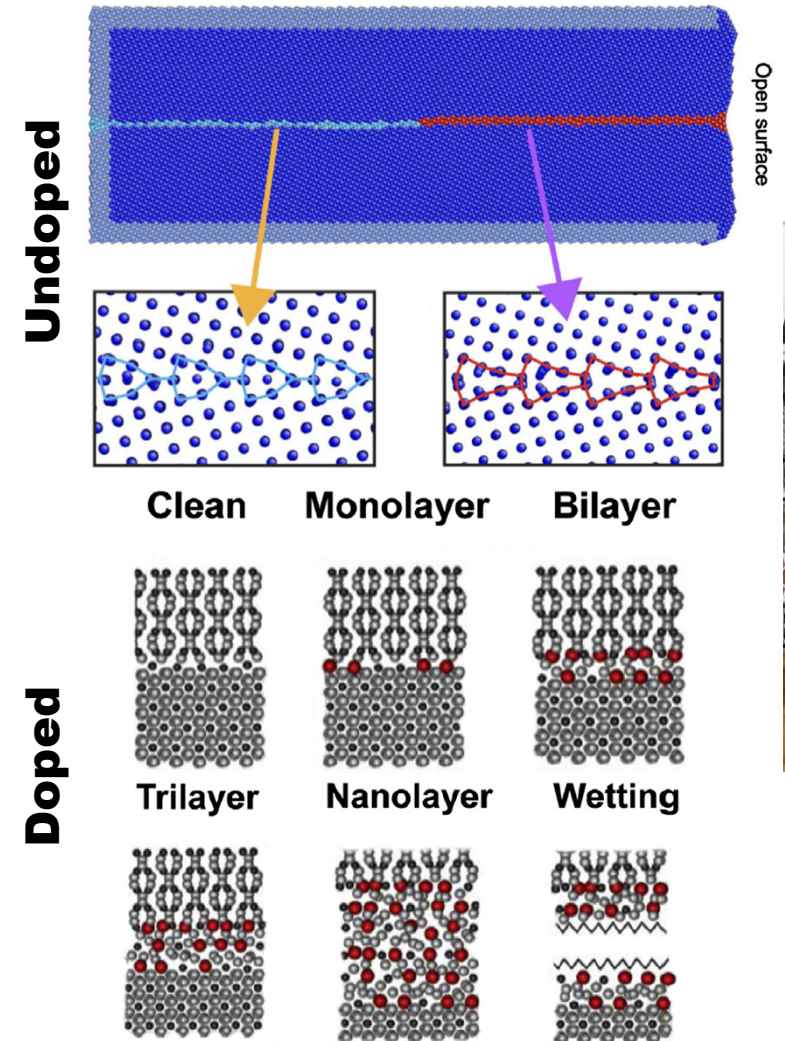
GBs have also distinct atomic and chemical structures

Complexions and complexion transitions



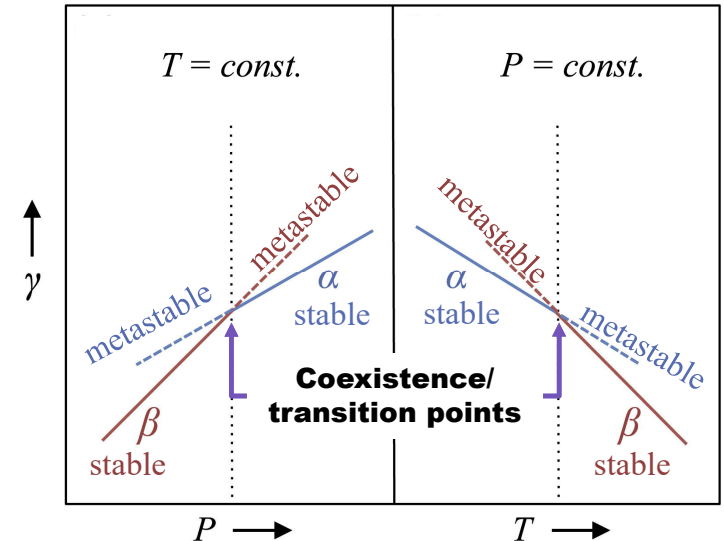
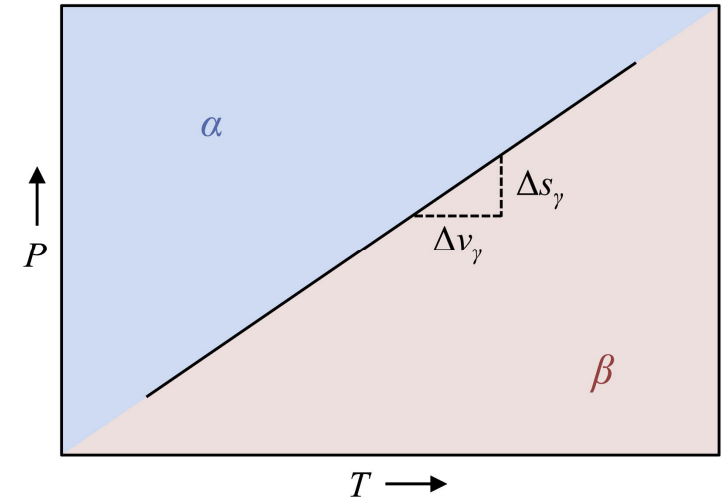
Basics about complexions and complexion transitions

- ♦ Grain boundaries are **not phases**
 - they **cannot exist independently**
 - only exist as a result of the adjacent grains
- ♦ Grain boundaries can undergo **structural transitions** (similar to phase transitions in bulk)
 - structures and structure transitions referred to as **complexions and complexion transitions**
- ♦ **Minimal description** of GB excess free energy / unit area γ depends on
 - bulk **thermodynamic state variables** (T, P, μ_i)
 - five macroscopic **interface parameters**:
 - 3 for misorientation R between adjacent grains faces
 - 2 for GB plane normal orientation (\hat{n})
- ♦ Other parameters exist such as excess of impurities/ dopants and point defects, structural/compositional gradients, microscopic displacement (e.g. disconnections), ...



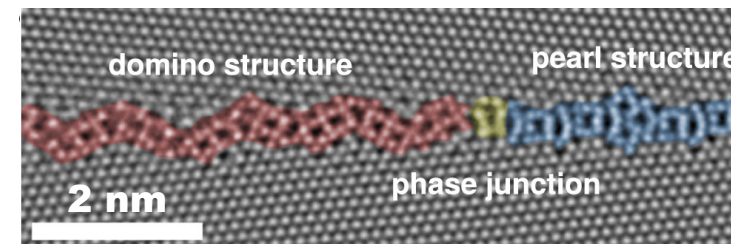
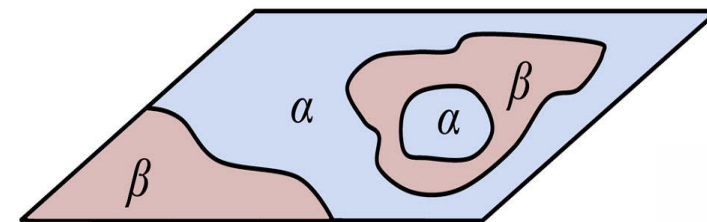
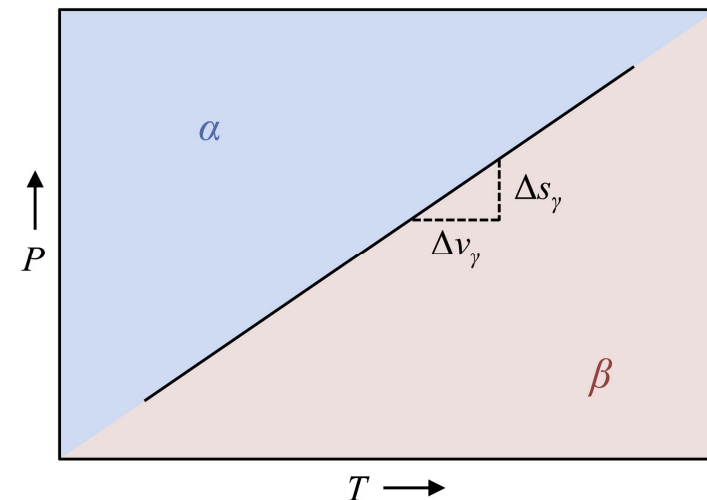
Basics about complexions and complexion transitions

- ♦ T, P subspace: **GB adopts complexion** associated **with lowest γ** (e.g. energy) for given T, P
 - GB of complexion type α stable for high P / low T
 - GB of complexion type β stable for high T / low P
- ➔ **Transition** occurs when **energy curves cross**
- ♦ Complexion transitions can be:
 - **first order** (γ continuous, $\partial\gamma$ discontinuous)
 - ➔ transition occurring on crossing of competing grain boundary free energy curves (e.g. clean to monolayer, ...)
 - **second order** ($\partial\gamma$ continuous, $\partial^2\gamma$ discontinuous)
 - ➔ gradual replacement of one type of grain boundary repeating structural unit for another (e.g. gradual replacement of GB units)



Complexion and complexion transitions

- ♦ **Coexistence line** between complexions α , β exists and defined by underlying thermodynamics
 - $\Delta \left(\frac{\partial \gamma}{\partial T} \right)_P = -\Delta s_\gamma$ (change in entropy)
 - **Discontinuity** in first derivative corresponds to **latent heat** ($Q = T\Delta S$) of complexion transition
 - $\Delta \left(\frac{\partial \gamma}{\partial P} \right)_T = -\Delta v_\gamma$ (change in GB volume)
 - **Discontinuity** in first derivative corresponds to **specific excess GB volume change**
- ♦ Proportion (i.e. character distribution) of coexisting complexions determined for example by internal stresses



Congruent vs non-congruent complexion transitions

◆ Congruent complexion transition

GB shape/geometry (misorientation vector R and GB normal \hat{n}) do not change during transition

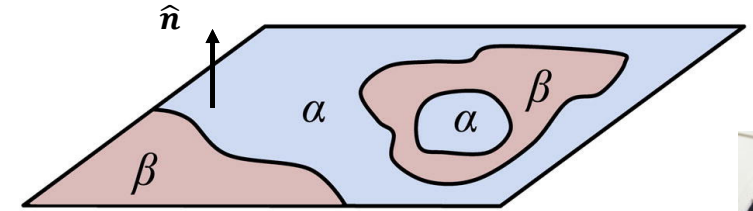
→ 5-parameter GB character remains constant (e.g. transition from monolayer to bilayer)

◆ Non-congruent transition:

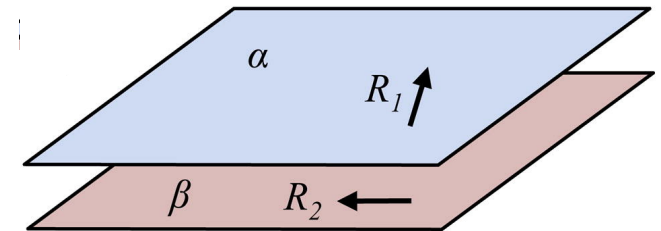
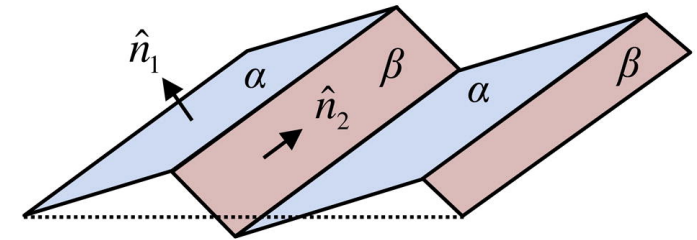
change in geometrical parameters (i.e. 5-parameter GB character)

- facet formation, where \hat{n} splits into components \hat{n}_1 and \hat{n}_2 whose weighted average is \hat{n}
- dissociation into two new interfaces separated by a wetting layer, which may be crystalline with well-defined misorientations $R_{1,2}$ whose sum is R , or non-crystalline where the original R is maintained across the spatial gap

Congruent



Non-congruent



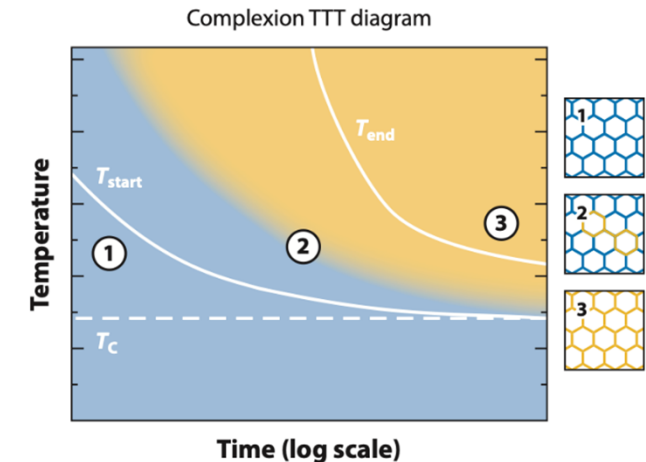
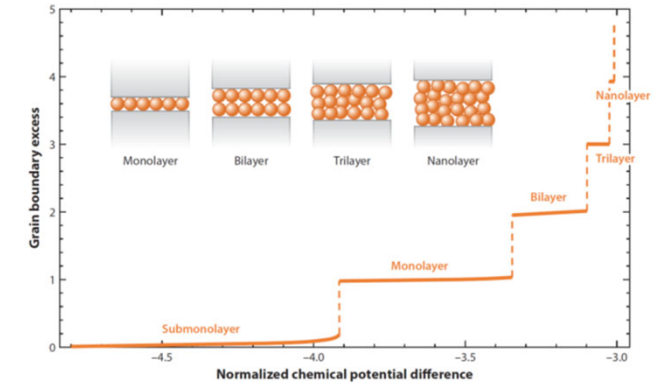
Thermodynamic description of complexion transitions

- ◆ Though **complexion transitions** are referred to as structural GB changes, they may involve **chemical composition changes in addition to structural rearrangement**
- ◆ **Grain boundary energy change** described as:

$$d\gamma = -[S]_{N_1}dT - [V]_{N_1}dP - \sum_{i=2}^C [N_i]_{N_1}d\mu_i$$

- [S]	excess entropy	- T	temperature
- [V]	excess volume	- P	pressure
- [N _i]	excess of component i at interface	- μ	chemical potential

- ◆ Complexion transitions lead to **discontinuous property changes** (e.g. GB mobility, GB energy, diffusivity,...)
 - ➔ Observation of discontinuous change in characteristics (e.g. GB mobility) indicator of complexion transition
- ◆ **Note:**
 - Transition** points are **specific to complexions themselves** (e.g. each complexion has its own)
 - ➔ Rapidity of change (and thus detectability) depends on proportion within material!

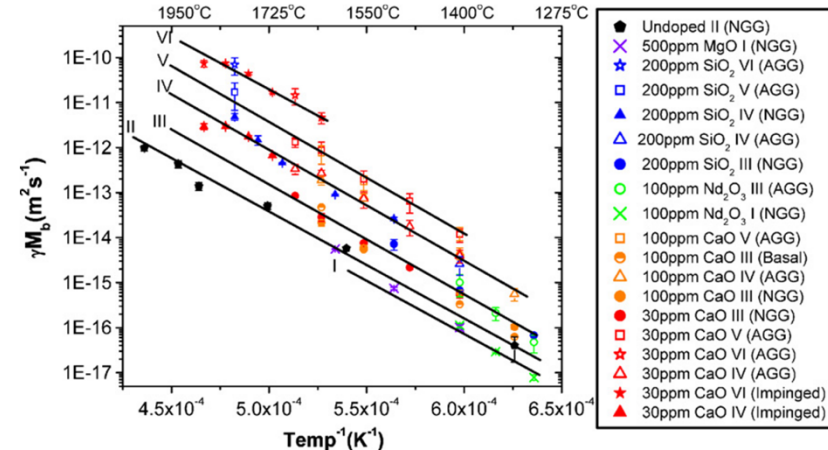
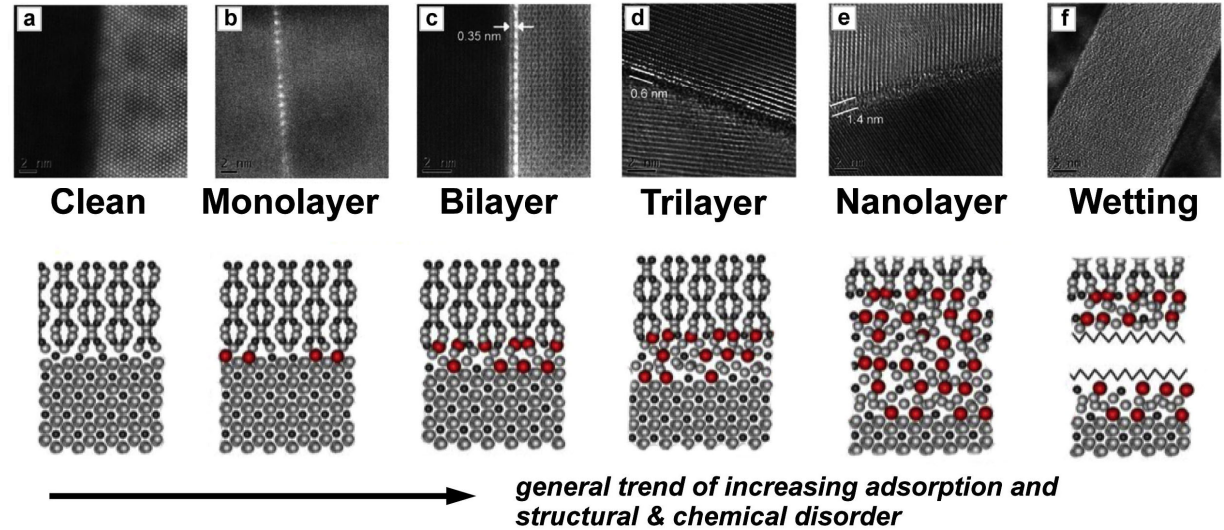


Congruent complexion examples

- ◆ **First order** (i.e. discontinuity in composition) complexion transitions observed in alumina
 - **Six discrete** "Dillon-Harmer" **complexions** (type I to VI)
 - GB thickness not arbitrary but rather determined by thermodynamic equilibrium conditions
- ◆ **Grain boundary mobilities** found to **increase with complexion thickness** from type I to type VI

Note:

Proof of existence of mobility increasing complexion transitions, does not per se negate the opposite!



Grain boundary energies and complexion transitions

- ◆ **Thermal grooving** of a polished surface followed by atomic force microscopy allows determining the **grain boundary energies**:

$$\gamma_{GB}/\gamma_S = 2 \cos(\Psi_S/2)$$

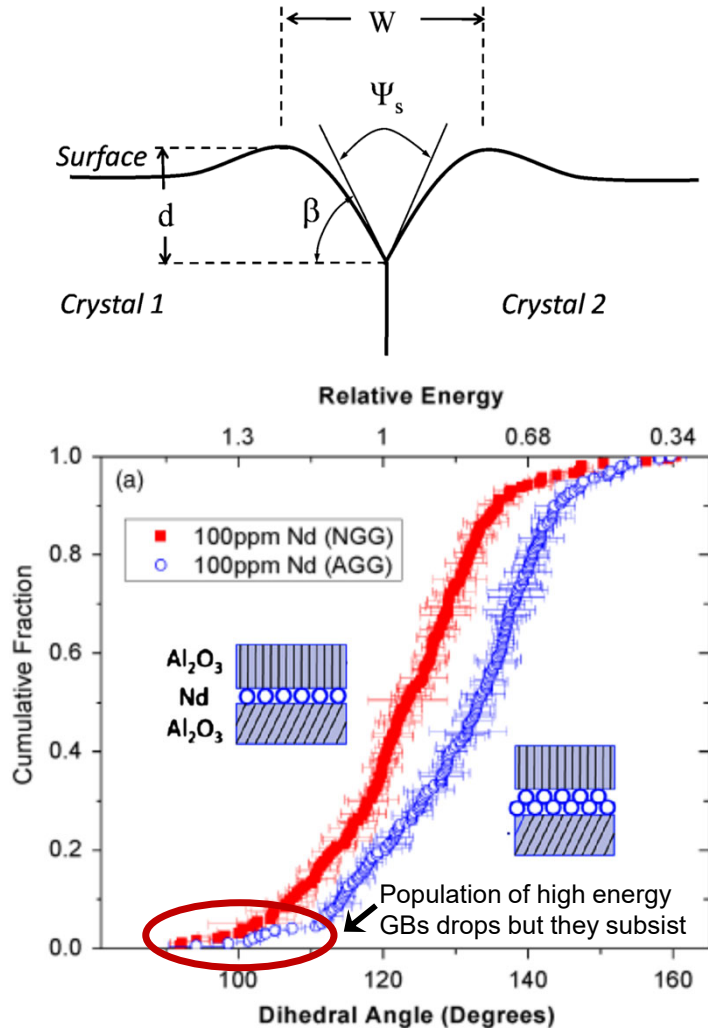
→ **Higher dihedral angles** Ψ_S represent **lower grain boundary energies** and vice-versa

- ◆ **Complexion transitions** effectively reduce grain boundary energies

→ Upon complexion transition occurrence **average grain boundary energy decreases**

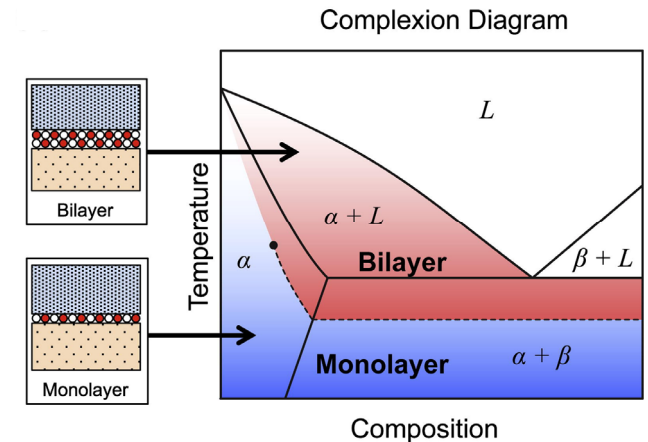
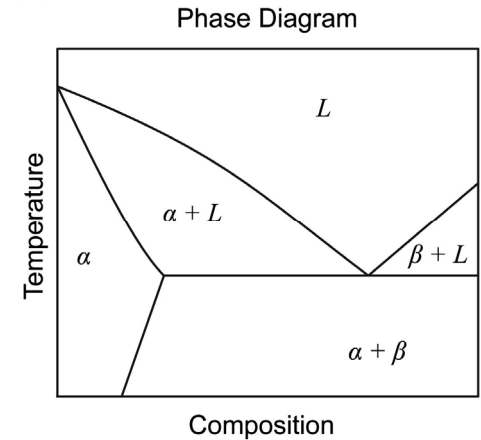
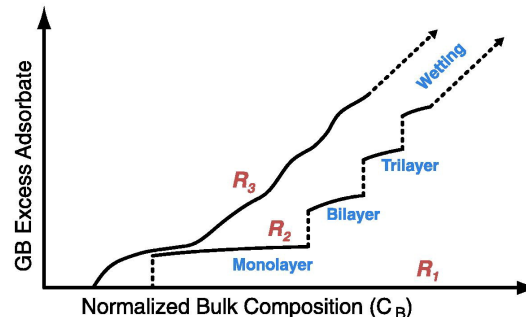
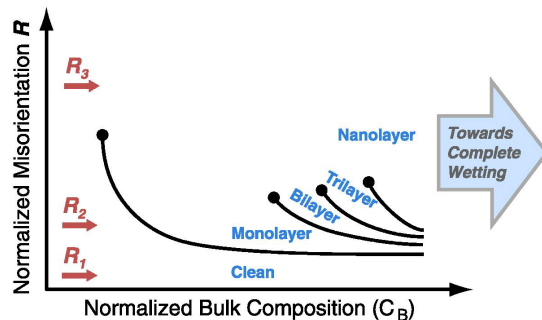
- ◆ **Grain growth** due to higher grain boundary mobility keeps forming **new grain boundaries**

→ Range of grain boundary energy distribution remains similar
→ Since complexion transitions reduce GB energy, **new GBs with high energy** must be **continuously formed**

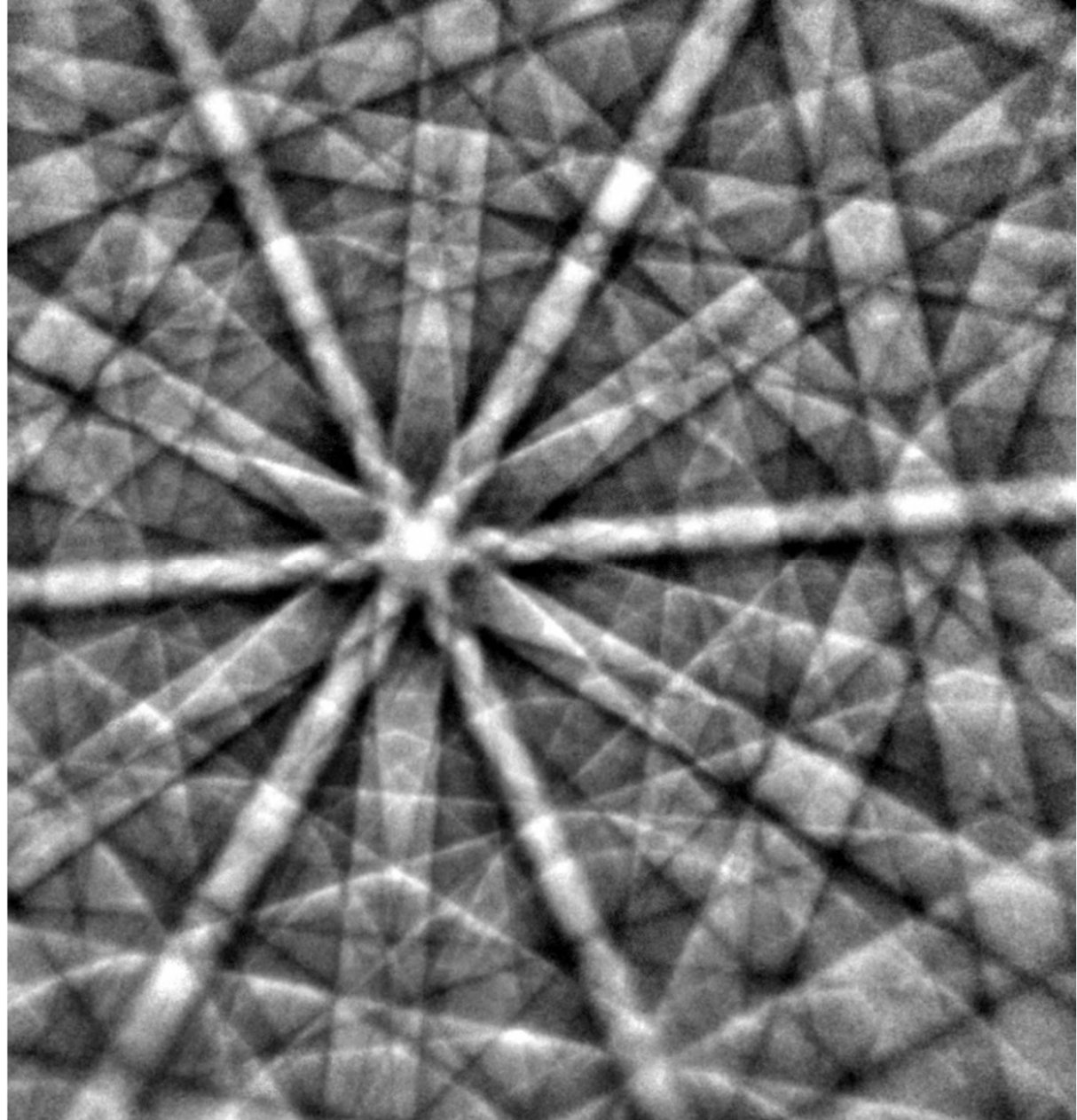


Complexion transition phase diagrams

- ◆ Efforts ongoing to understand complexions to extend needed to generate **engineering diagrams** and relate to macro-properties
- ◆ Due to multi-dimensionality of complexion parameters (by opposition to phase transitions) **parameter space must be reduced** for plotting
→ complexion diagrams only **stability guide**
- ◆ **In general:** Complexion transitions favored by **increasing temperature and dopant concentration**
- ◆ **Note:**
Not all complexion types possible for all grain boundary characters (R and \hat{n}) and e complexion depends on misorientation between sides of GB



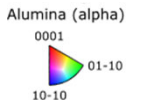
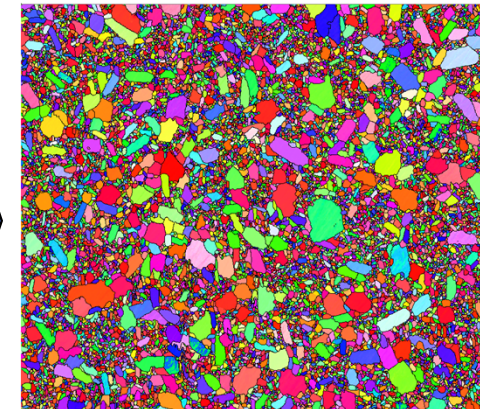
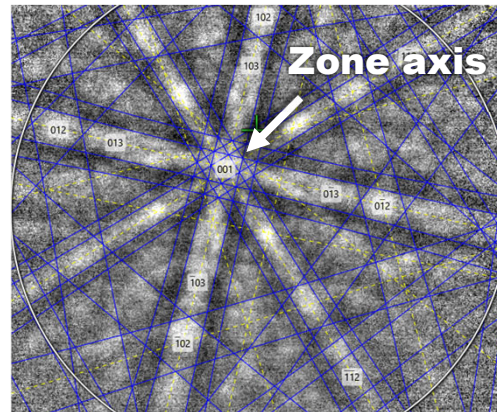
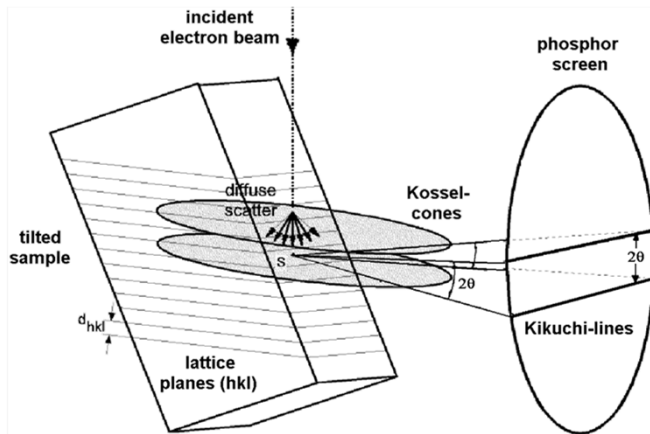
Basics about EBSD analysis



EBSD basics

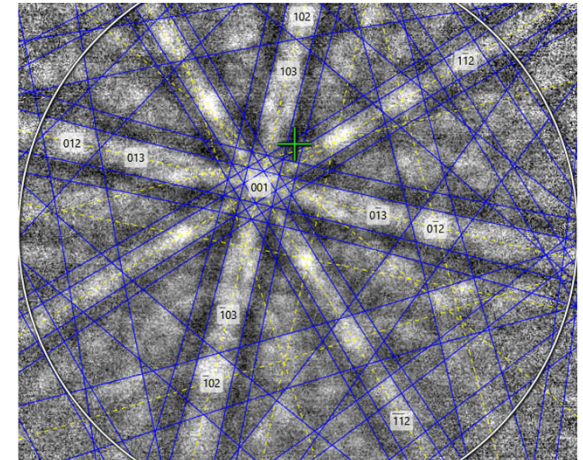
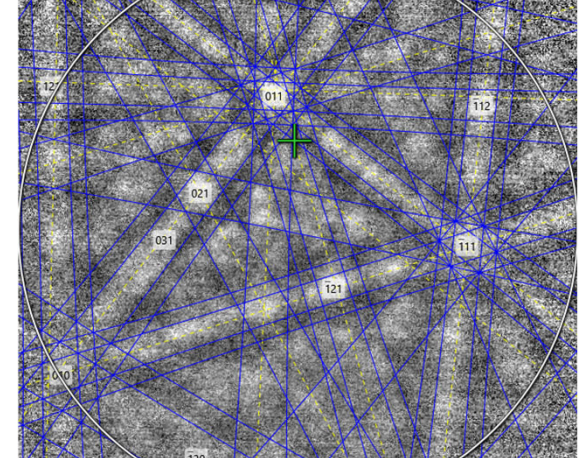
♦ EBSD basics (short reminder):

- For specific atomic planes electrons satisfy Bragg's law: $n\lambda = 2d \sin \theta$
→ **Elastically scattered**, creating intense coherent wavefronts
- Electrons undergo multiple diffuse elastic scattering interacting with periodic lattice
→ **Kossel cone** formation
- Interaction of Kossel cones with camera/phosphor
→ **Kikuchi lines** corresponding to family of hkl planes
- Intersection of Kikuchi bands forms pattern **uniquely identifying crystal orientation**
→ Possible to attribute **crystal orientation on a point-by-point basis** → EBSD maps



Additional background on EBSD basics

- ◆ For **10–30 keV electrons**, small Bragg angles ($1\text{--}5^\circ$) lead to **nearly straight Kossel cone traces**
- ◆ On phosphor screen, Kossel cone pair from specific hkl lattice planes form Kikuchi lines, bounding the Kikuchi band
- ◆ Kikuchi **band width proportional to d -spacing** of the diffracting hkl lattice plane
- ◆ Indexing (Miller indices) done by comparing measured interplanar angles with known crystal structures (.cif file)
→ **Crystal structure has to be known!**
- ◆ A consistently indexed triplet of lattice planes from different zones determines the crystal orientation
- ◆ Detected lattice plane positions have errors
 - Multiple potential crystal orientations possible
 - Different confidence and quality measures performed to find best (i.e. most likely) solution
- ◆ **High quality EBSD maps**
= High quality sample preparation !



Orientation dependent Kikuchi patterns in a cubic crystal with automated line tracing and indexing in AZtec

Euler angles

◆ Euler angles

set of **3 angles describing crystal orientation relative to a fixed reference frame**

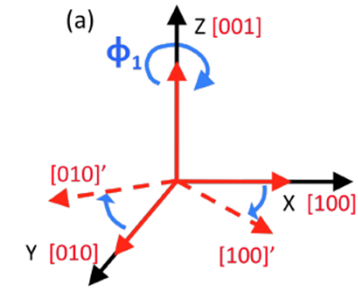
- Angles denoted as (ϕ_1, θ, ϕ_2) or (α, β, γ) , depending on convention
- ◆ Euler angles typically define transformation angles **from sample to crystal reference** frame (i.e. coordinate system)
 - Orientation of each grain on EBSD map defined by its Euler angles
 - Rotation matrix $R = R_z(\phi_1)R_x(\theta)R_z(\phi_2)$

◆ Note:

Reference frame can be freely chosen depending on analysis requirements

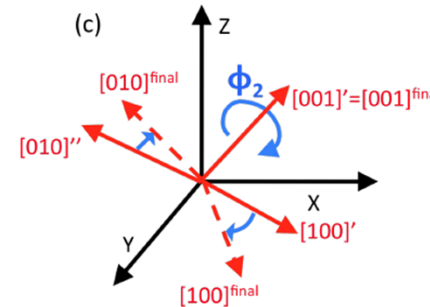
- **Crystal reference frame**
 - Grain boundary plane distribution
- Bi-crystal reference plane
 - Grain boundary character distribution

1st rotation: ϕ_1 around the Z-axis



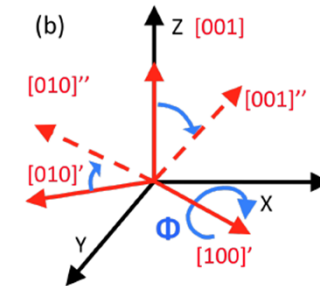
$$R_z(\phi_1) = \begin{bmatrix} \cos \phi_1 & -\sin \phi_1 & 0 \\ \sin \phi_1 & \cos \phi_1 & 0 \\ 0 & 0 & 1 \end{bmatrix}$$

3rd rotation: ϕ_2 around the Z-axis



$$R_z(\phi_2) = \begin{bmatrix} \cos \phi_2 & -\sin \phi_2 & 0 \\ \sin \phi_2 & \cos \phi_2 & 0 \\ 0 & 0 & 1 \end{bmatrix}$$

2nd rotation: θ around the X-axis



$$R_x(\theta) = \begin{bmatrix} 1 & 0 & 0 \\ 0 & \cos \theta & -\sin \theta \\ 0 & \sin \theta & \cos \theta \end{bmatrix}$$

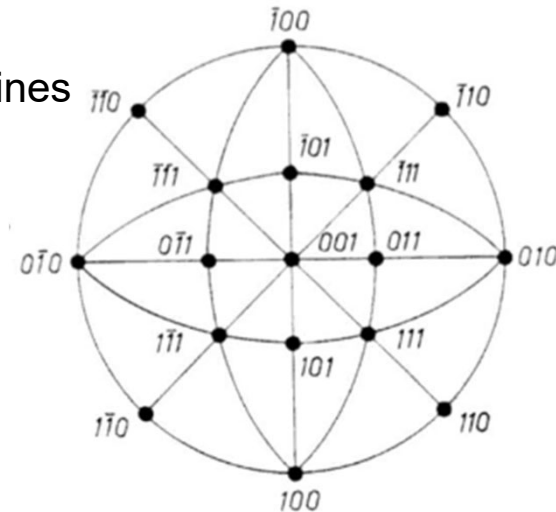
Stereological projections – Construction principle

♦ Stereographic projection

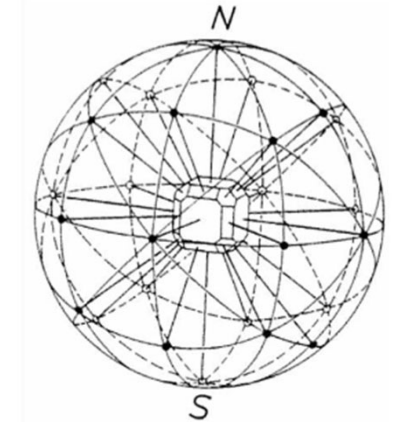
Maps lattice directions and plane normals from a sphere onto an equatorial plane, preserving angular relationships

♦ Construction of stereographic projection

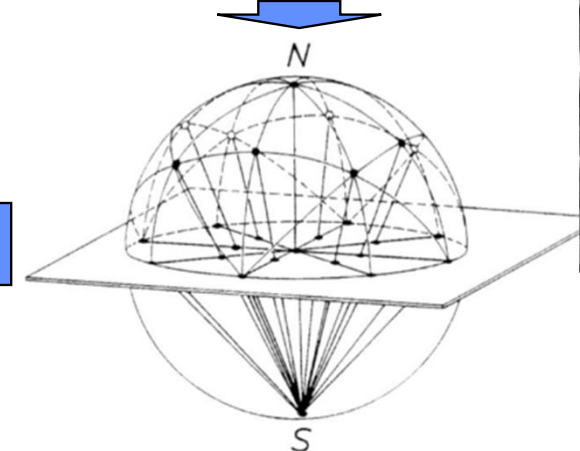
- Position **crystal at the center** of the pole sphere
- Determine the **intersections** of lattice directions or plane normals **with the pole sphere**
- **Connect each intersection point to the opposite pole** using straight lines
- Stereographic projection is the **intersection** of those lines **with equatorial plane** of sphere



Stereographic projection of the upper hemisphere of (here) a cubic crystal



Cubic crystal placed in the center



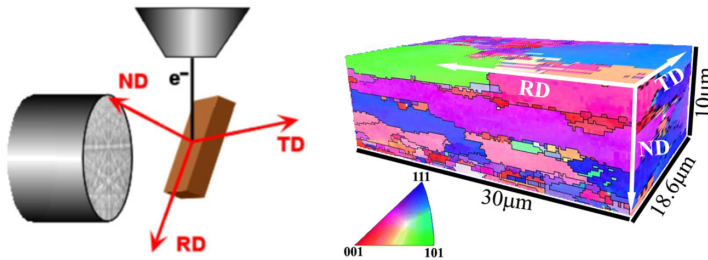
Projection onto the equatorial plane

Classical EBSD analysis: Pole figures

- ♦ Maps **distribution** of specific **crystallographic directions** (e.g. [111], [100], ...) relative to **sample's macroscopic reference frame**

- Axes (RD and TD) defined by sample orientation in reference frame
- Used to represent texture

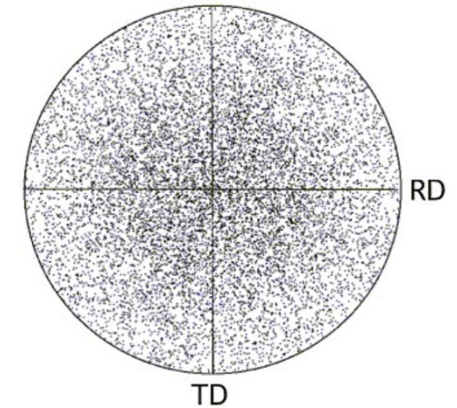
Defintion of Tilt and Rolling directions



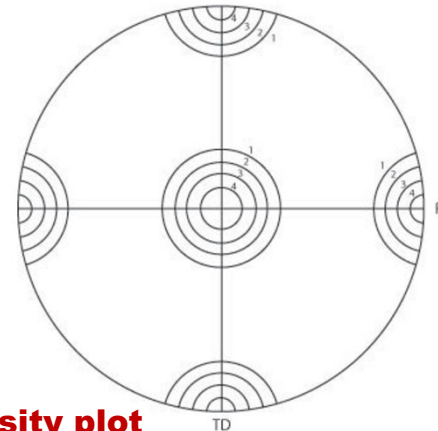
♦ Note:

- **Point accumulation near pole figure center** may be apparent for randomly oriented samples due to **angular distortions**
- When representing **large number of grains**, **pole overlap** on the pole figure obscures true orientation density → **use contour lines**

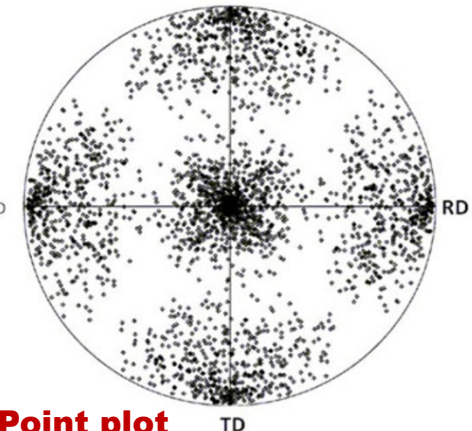
Without preferred orientation/texture



«cube» texture: preference for {100} orientations



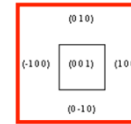
Density plot



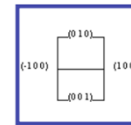
Point plot

Classical EBSD analysis: Inverse pole figures

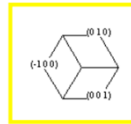
- ♦ Maps **relationship** between a specific **sample direction** (e.g. RD) **and crystal lattice**
 - Illustrated how crystal lattice is oriented relative to the macroscopic sample direction
 - Used to represent preferred grain alignment
- ♦ **Note:**
 - Shape and size of smallest domain containing all symmetrically non-equivalent directions depends on Laue group of respective crystal
 - Referred to as fundamental zone



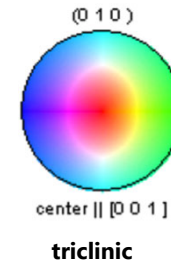
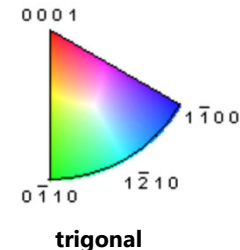
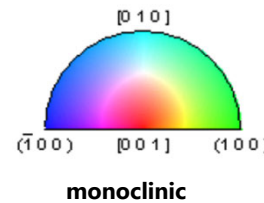
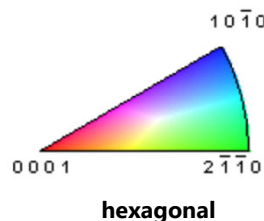
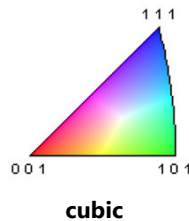
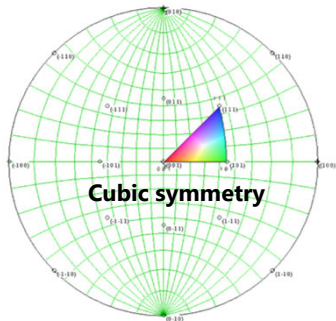
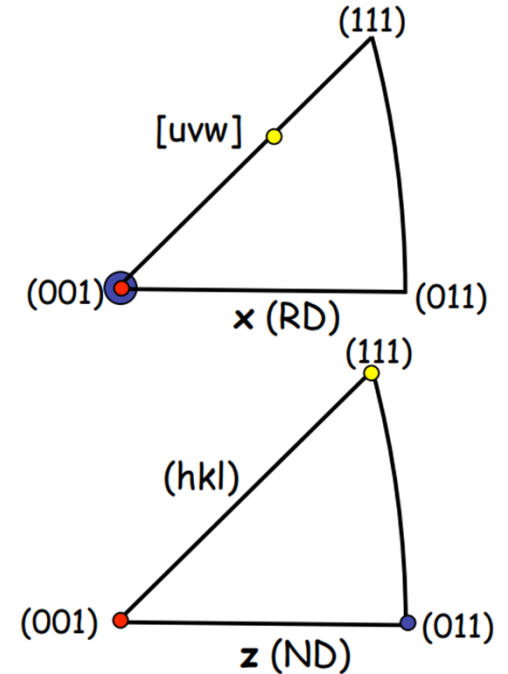
(001)[100]



(011)[100]



(-111)[211]

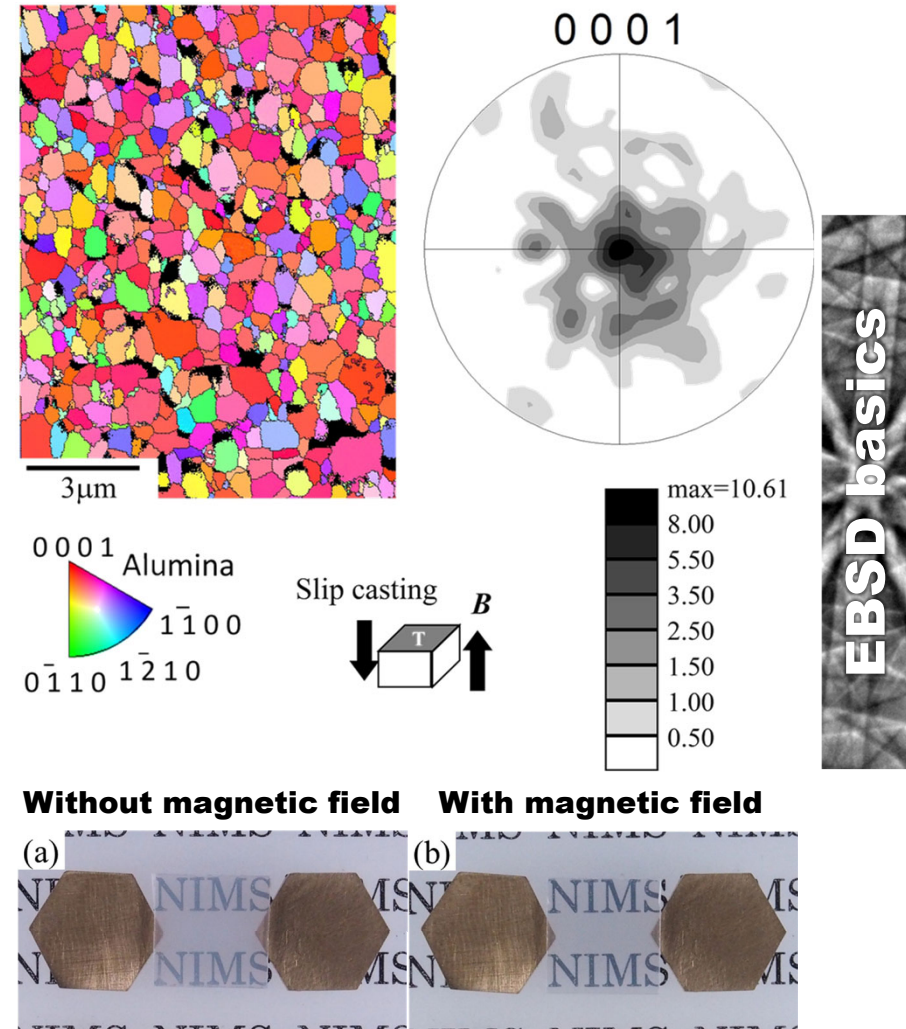


Fundamental zone of typical crystal systems

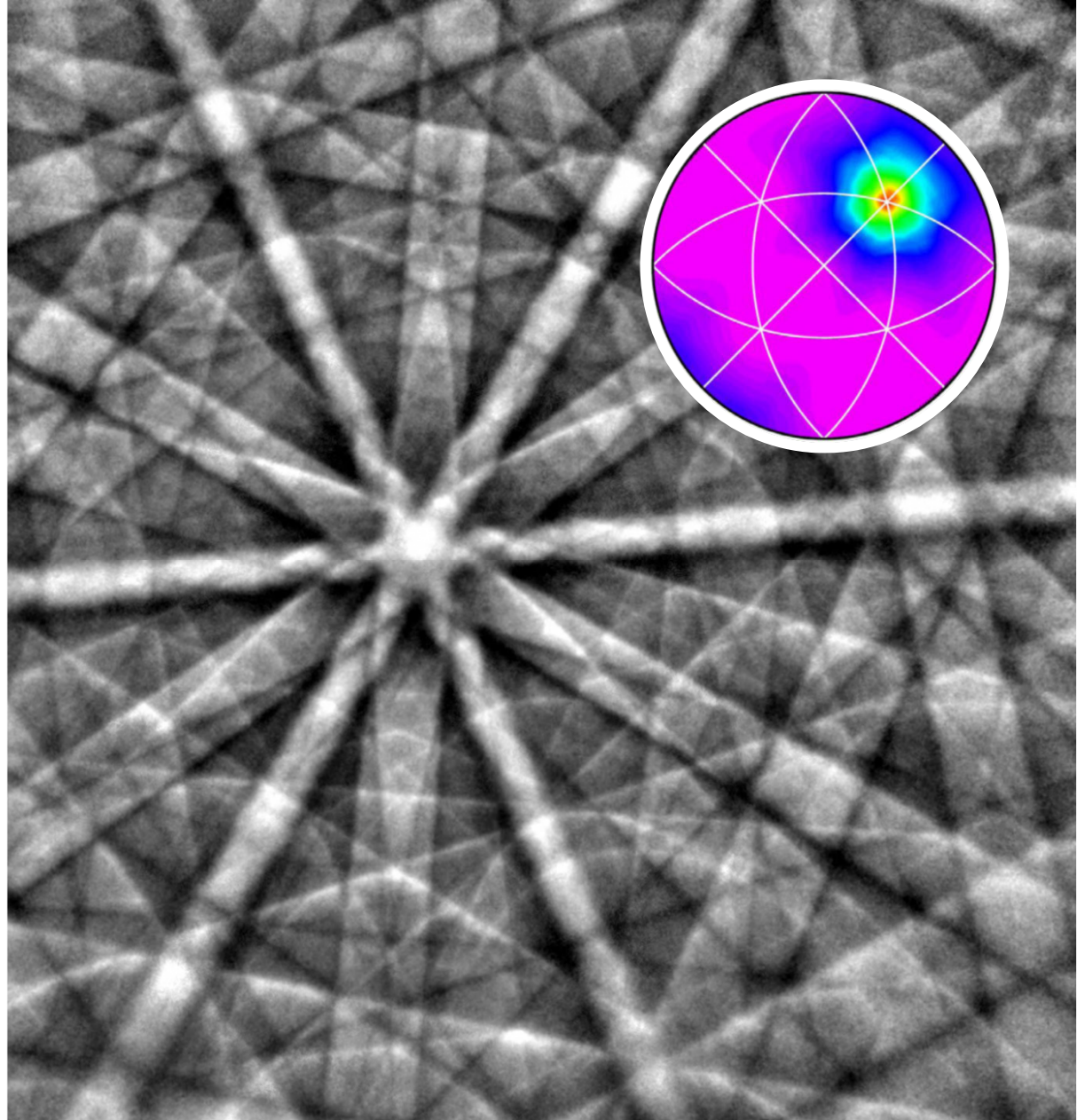
Stereological projections – Case study

Effect of crystallographic orientation on transparency of PCA prepared using magnetic alignment and SPS

- ◆ EBSD map and the pole figure obtained from EBSD analysis of T plane perpendicular to magnetic field
- ◆ Most grains are red, orange and yellow indicating $\{0001\}$ plane orientations with small angle deviations
→ $\{0001\}$ plane clearly aligned with T plane
- ◆ Also confirmed by transparency
→ Alignment suppresses/reduces birefringence effect at grain boundaries
→ Improved transparency confirms grain alignment along optical axis (e.g. $\{0001\}$)

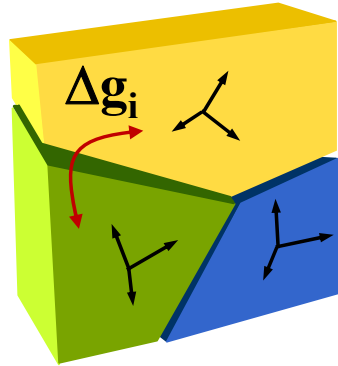


**5-parameter GB
character distribution
-
Stereological EBSD
analysis**



Grain boundary characterization problem

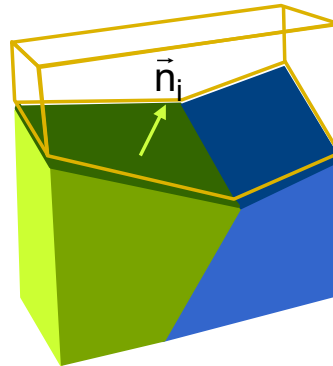
- ♦ A grain boundary is defined by 5 macroscopic parameters:



three to describe the misorientation



Directly computed from EBSD mapping data in commercial software



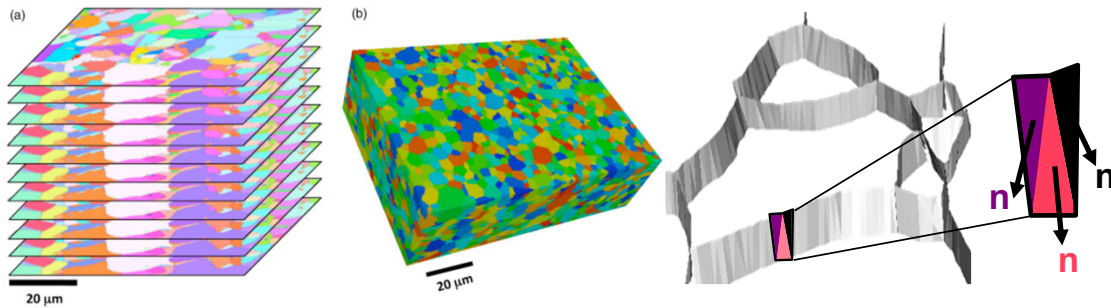
two for defining the GB plane orientation



Characterization approaches

- ♦ Two methods to determine the grain boundary plane:

1 FIB-EBSD-Nanotomography (3D EBSD technique)



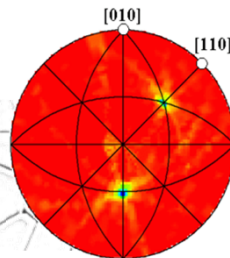
- ♦ Serial sectioning and EBSD acquisition
- ♦ Extract directly grain boundary character distribution from a specific sample area
→ typically less available!

2 Stereological EBSD analysis



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- ♦ More time-efficient and cost-effective than most 3D techniques
- ♦ Provides accurate estimates and offers statistical data from the entire sample
- ♦ But: Requires large datasets
No direct 3D reconstruction of specific grains or grain boundaries

Stereological EBSD

Stereological analysis method

◆ Stereology

Statistical method to estimate 3D structural properties from 2D cross-sections

◆ Stereological EBSD analysis

Statistical method to determine grain boundary character distributions from 2-dimensional EBSD maps

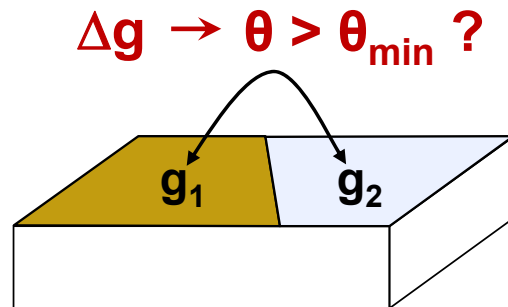
GB detection



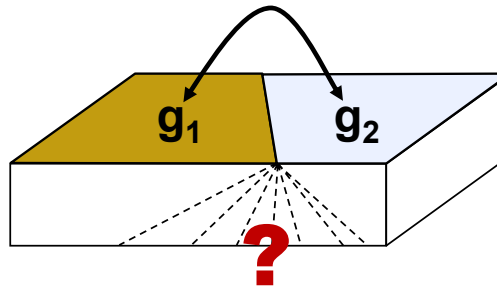
Problem statement



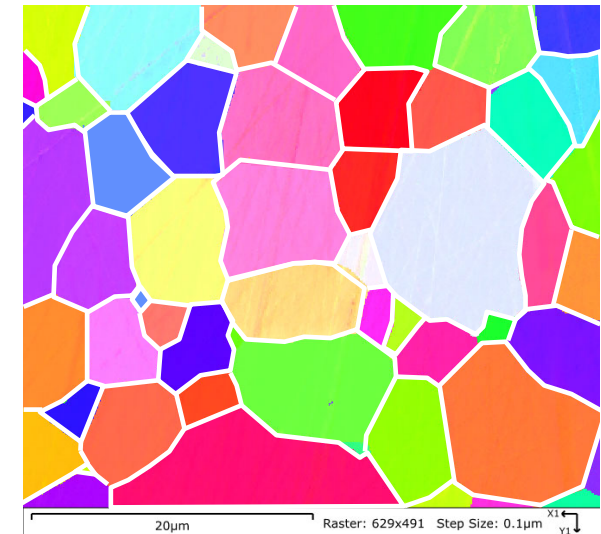
GB trace analysis to define GB segments



θ_{\min} needed to avoid fake GB generation



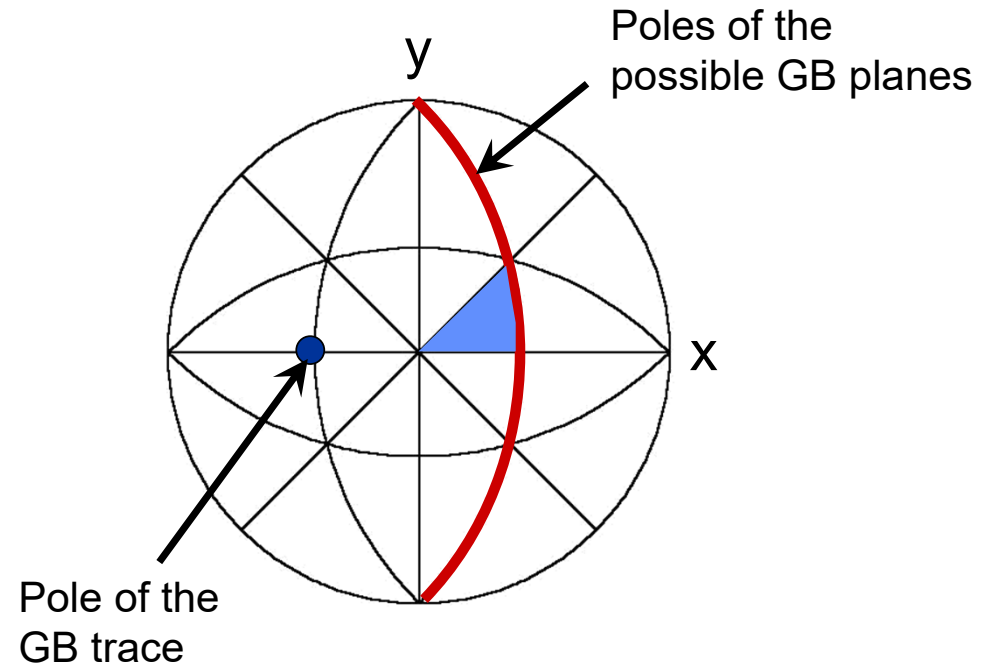
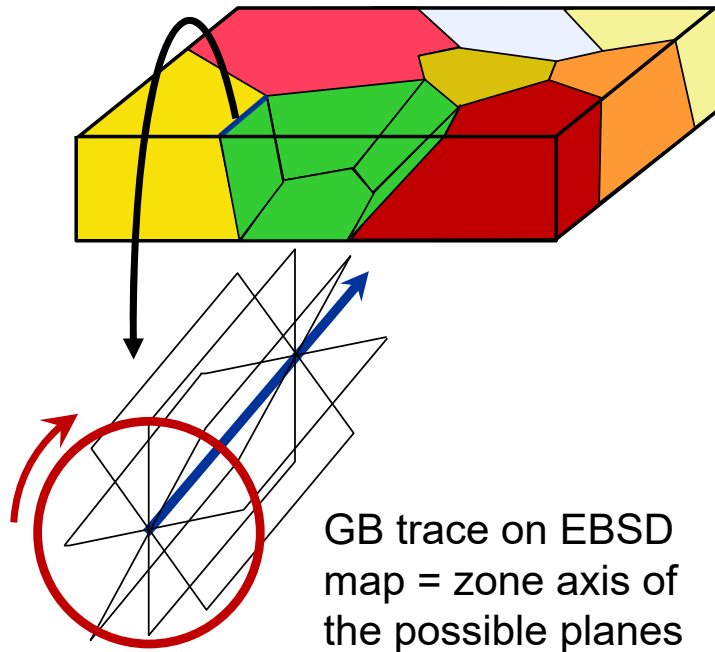
Missing:
GB plane orientation!



Stereological EBSD

Stereological analysis method

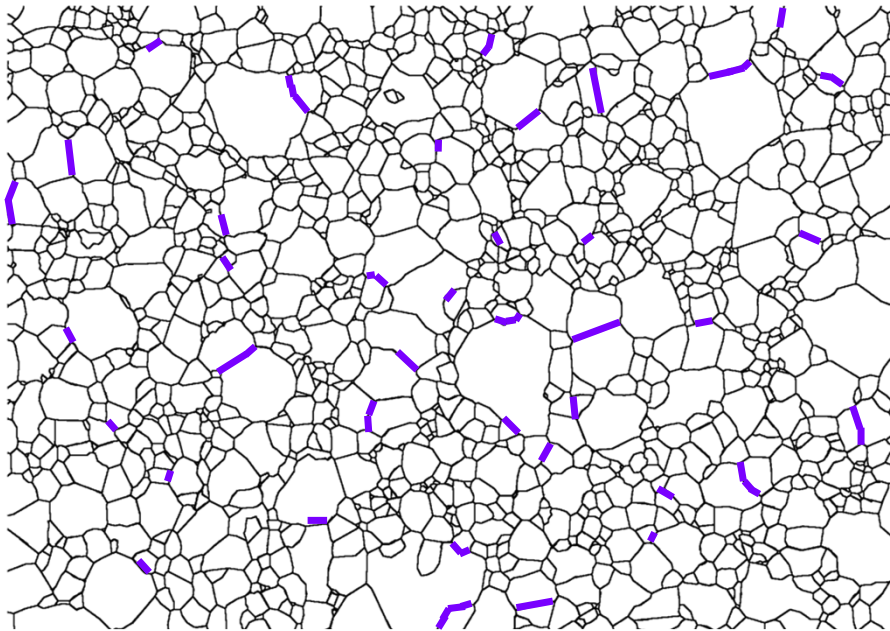
- ◆ From the GB trace analysis we know the zone axis of possible GB planes for each segment:



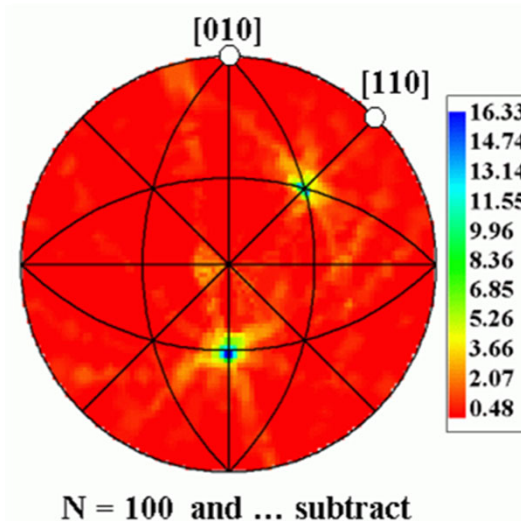
Stereological analysis method

- ◆ Superpose the poles of possible GB planes for GBs with a fixed Δg :

Grain boundary traces in sample reference frame



All planes in the zone of trace, in the misorientation frame (at a fixed Δg)

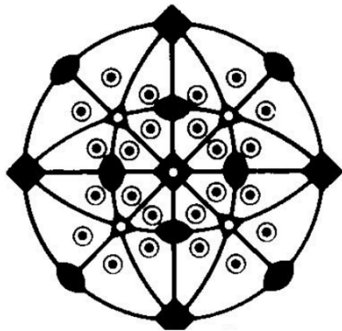


The **result** is a representation of the **true distribution of grain boundary planes at each Δg**

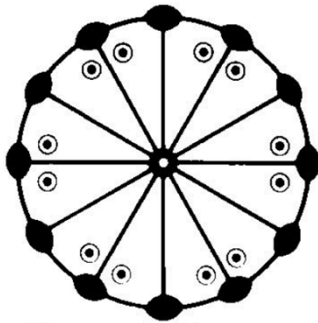
A continuous distribution requires roughly 2000 traces for each Δg

Stereological analysis method – data requirements

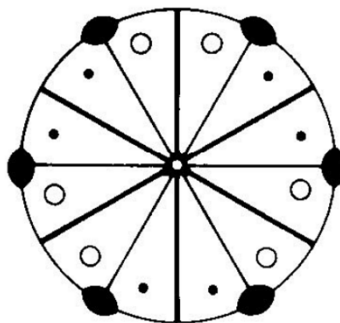
- ♦ Max step size allowed for EBSD mapping function of grain size distribution
→ ≥ 3 points per grain boundary required
- ♦ Amount of line segments required for statistically reliable analyses depends on crystal symmetry
→ Higher symmetry reduces fundamental zone and thus required data amount



Cubic (m-3m)



hexagonal (6/mmm)



trigonal (-3m1)

Lattice symmetry	Line segments number requirement	
	$\lambda(\Delta g, n)$ mode	$\lambda(n)$ mode
cubic	0.5×10^4	0.2×10^4
hexagonal	20×10^4	0.5×10^4
tetragonal	45×10^4	1×10^4
trigonal	180×10^4	1×10^4

**Grain boundary
character
distribution**

**Grain boundary
plane
distribution**

Stereological analysis method – GBCD representation

1-parameter GBCD

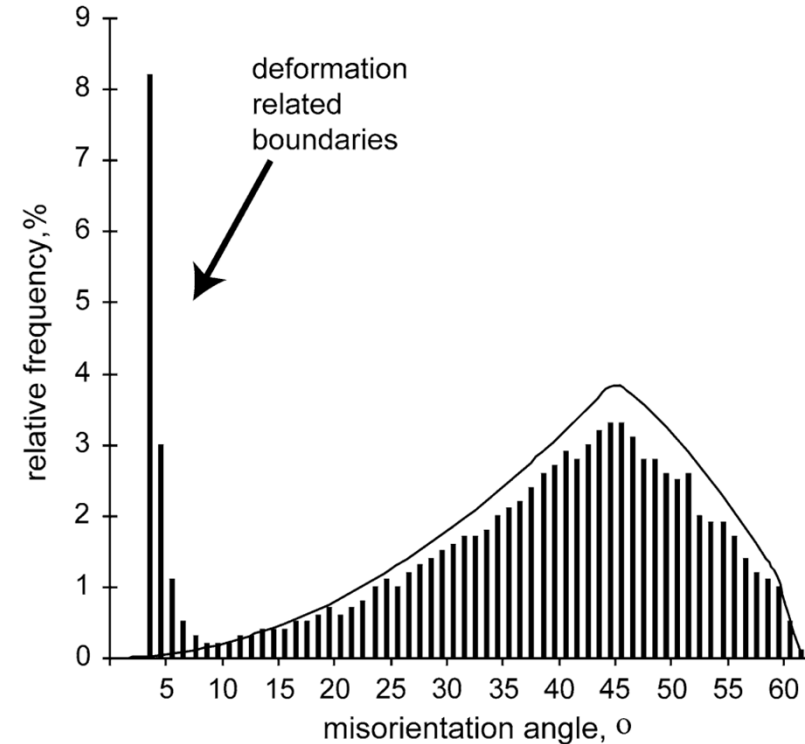
2-parameter GBCD

3-parameter GBCD

5-parameter GBCD

Misorientation angle distribution

- ◆ Represents grain boundary population as a function of minimum misorientation angle of each boundary
- ◆ max. possible misorientation is limited by crystal symmetry (example for trigonal 104.47°)



Misorientation angle distribution for NaCl after low strain deformation

Stereological EBSD

Stereological analysis method – GBCD representation

1-parameter GBCD

3-parameter GBCD

2-parameter GBCD

5-parameter GBCD

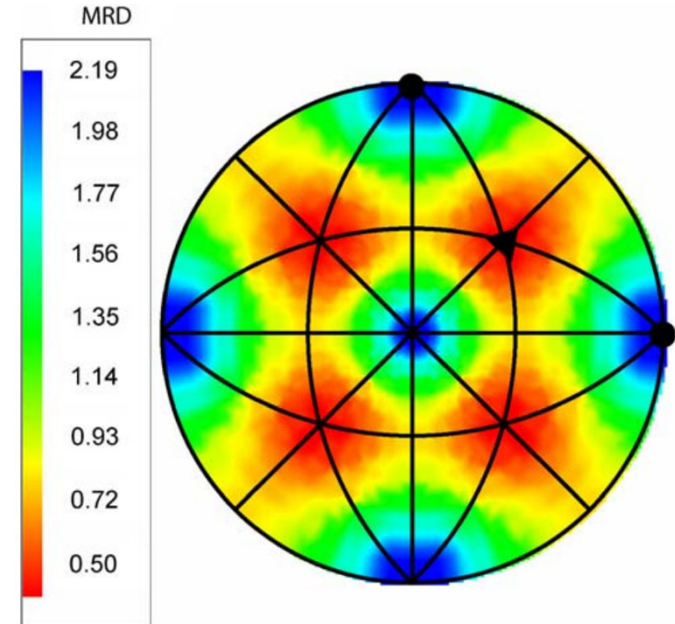
Grain boundary plane distribution (GBPD)

◆ Parameters:

- 1 normal of the grain boundary line segment
- 1 angle of inclination of the grain boundary

◆ Independent of misorientation angle

- ◆ Typically plotted on stereograms looking down the [001] direction
- ◆ Plot: Full stereogram or fundamental zone



GBPD for all planes averaged over all misorientations in NaCl after low strain deformation

Stereological EBSD

Stereological analysis method – GBCD representation

1-parameter GBCD

2-parameter GBCD

3-parameter GBCD

5-parameter GBCD

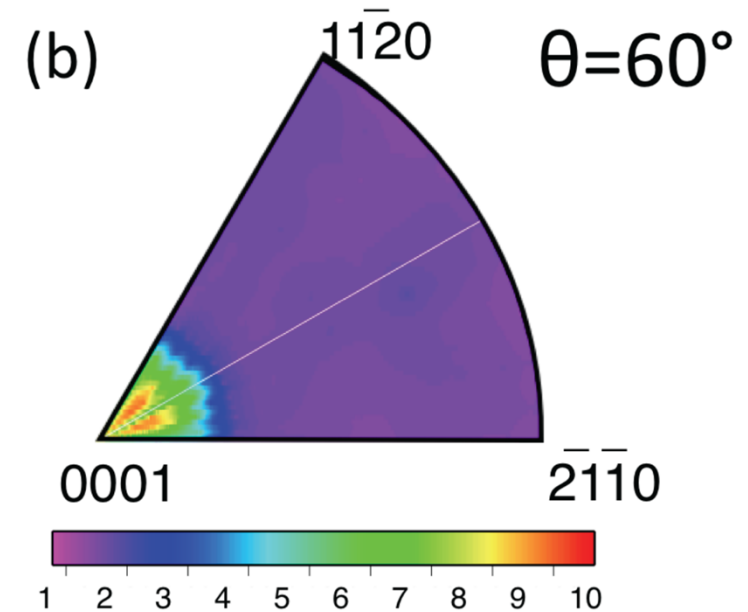
Misorientation distribution function in the Rodrigues-Frank space

◆ Parameters:

- 1 for the misorientation angle
- 2 for the rotation axis between adjacent grains

◆ Plot: Sections of axis angle space

- ◆ Allows identifying around which crystal axis adjacent grains are preferentially rotated as a function of the angle
(**independent of the grain boundary plane**)



Section of the 3D misorientation distribution in alumina in axis-angle pair format

Stereological EBSD

Stereological analysis method – GBCD representation

1-parameter GBCD

2-parameter GBCD

3-parameter GBCD

5-parameter GBCD

Grain boundary character distribution

(combining 2-parameter and 3-parameter GBCD)

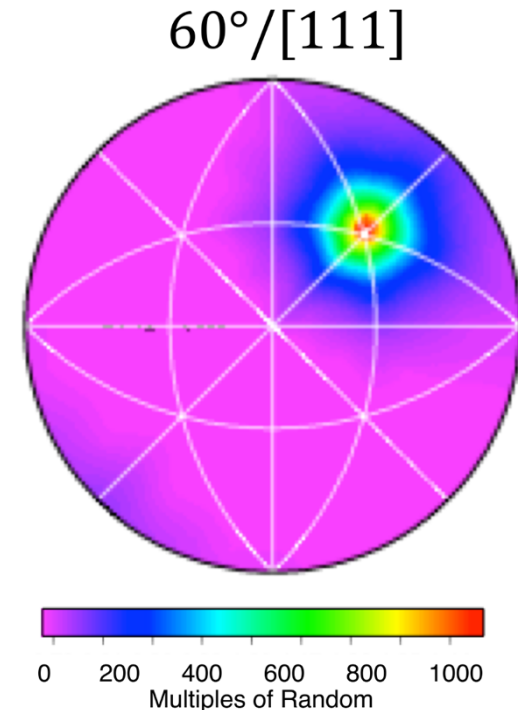
◆ Parameters:

- 3 for the misorientation
- 2 for the grain boundary plane normal
- Full geometric parameter description

◆ Plot: Always shown in full stereogram

◆ Plots distribution of grain boundary planes at fixed misorientation angle around specified axis

→ **Full geometric description of grain boundary**



**GBCD at a 60°/[111] misorientation ($\Sigma 3$)
for Ni**

Effect of complexion transitions on grain boundary plane/character distribution



Effect of dopants on GBPD

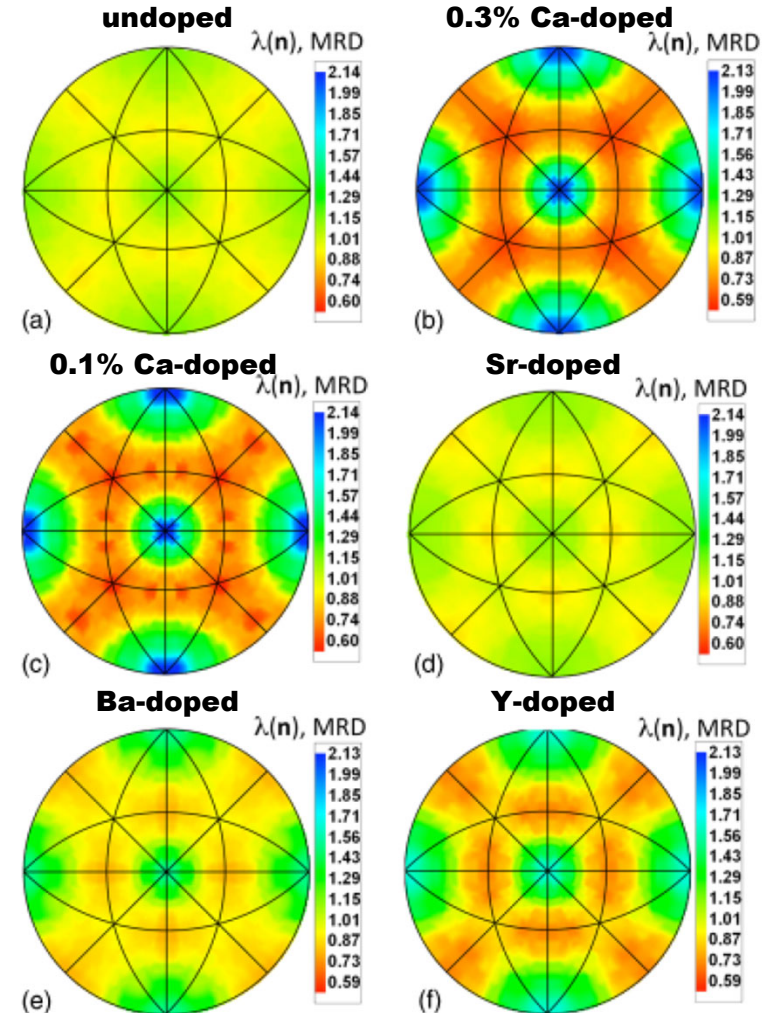
- ♦ Dopants change grain boundary energies which may directly affect grain boundary population

Example: MgO sintered for 15 hours to reach a thermodynamic “equilibrium”

- ♦ Especially Ca- and Y-doping lead to significant GBPD changes
- ♦ Ca-doping strongly favors occurrence of {100} planes
- ♦ Sr-doping has minor effect on GBPD

What is the role of complexion transitions ?

MgO samples sintered at 1600°C for 15h and thermally etched at 1400°C for 2-5h



Complexion effects

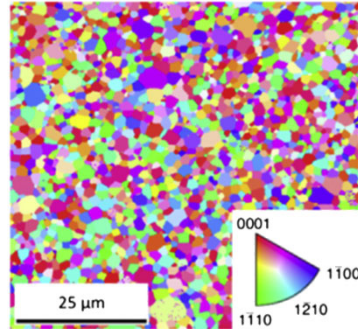
Effect of complexion transitions on GBPD

Example of Y-doped alumina

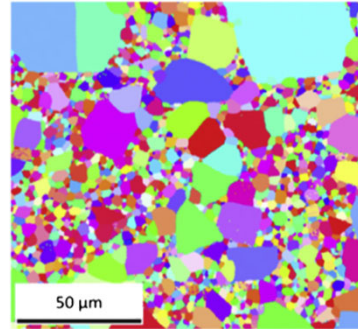
Sintering temperature
changed to prevent/trigger
complexion transition!

Microstructure

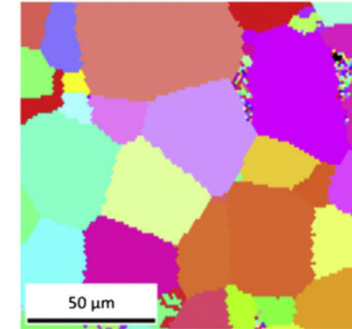
1400°C



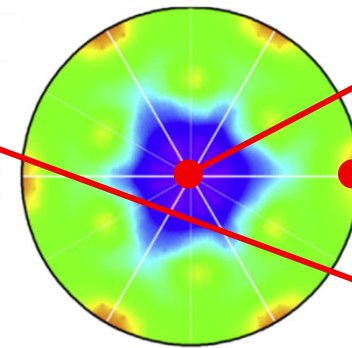
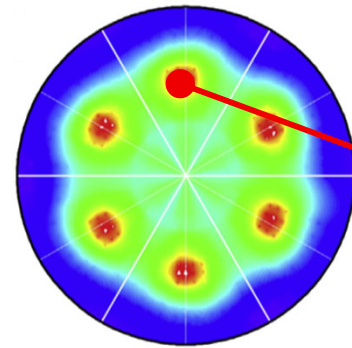
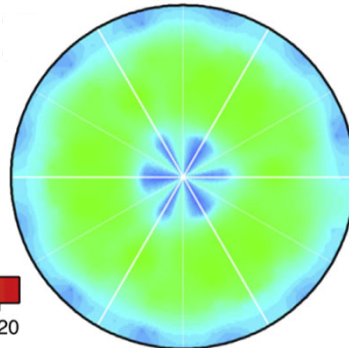
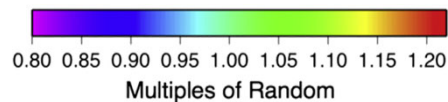
1500°C



1600°C



Stereological
projection of
grain boundary
plane distribution



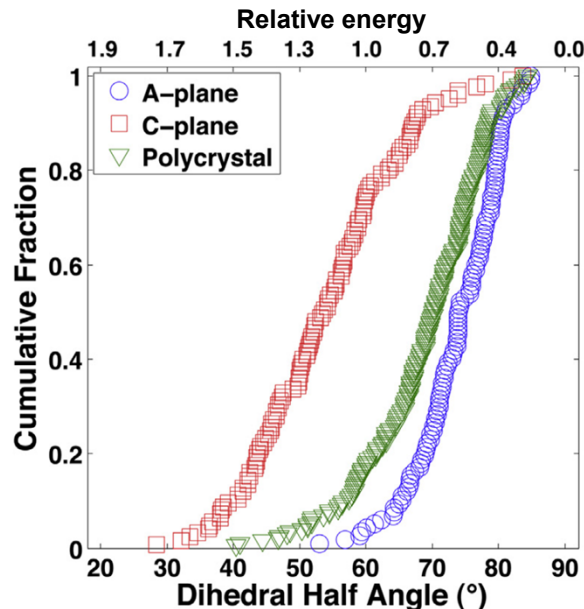
[0001]
C planes (basal)
[11 $\bar{2}$ 0]
A planes
[1 $\bar{1}$ 02]
R planes

**Grain growth needed to modify the grain boundary population!
Results suggest that R-planes in Y-doped alumina move faster!**

Effect of grain boundary energy on complexion transitions

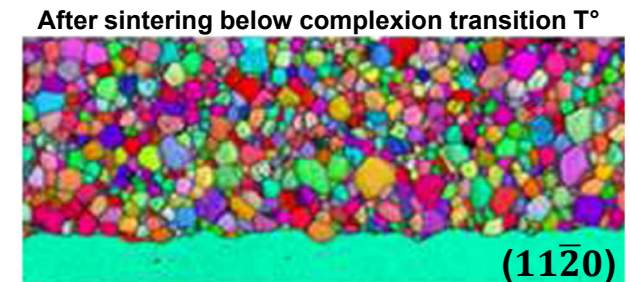
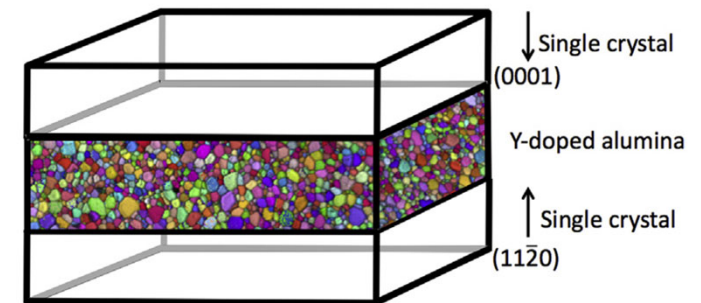
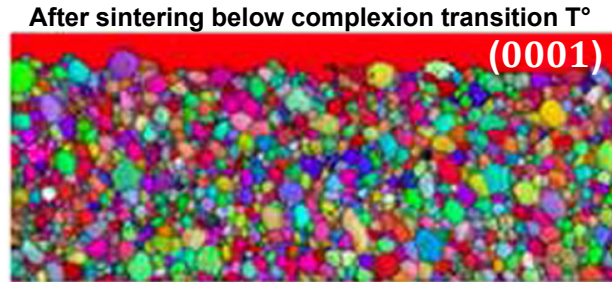
Example of Y-doped alumina

- ◆ Complexion transitions reduce grain boundary energy
→ previous slide: energy higher for $\{0001\}$ planes than for $\{11\bar{2}0\}$ or $\{1\bar{1}02\}$ planes
- ◆ Co-sintering of powder with single crystals to study grain boundary energy effect on complexion transitions



- ◆ After sintering at 1300°C (i.e. below complexion transition T°)

- No microstructural difference between C- and A-plane interface
- Average grain boundary energies higher for C- than A-plane interface or random distribution (i.e. polycrystal bulk)



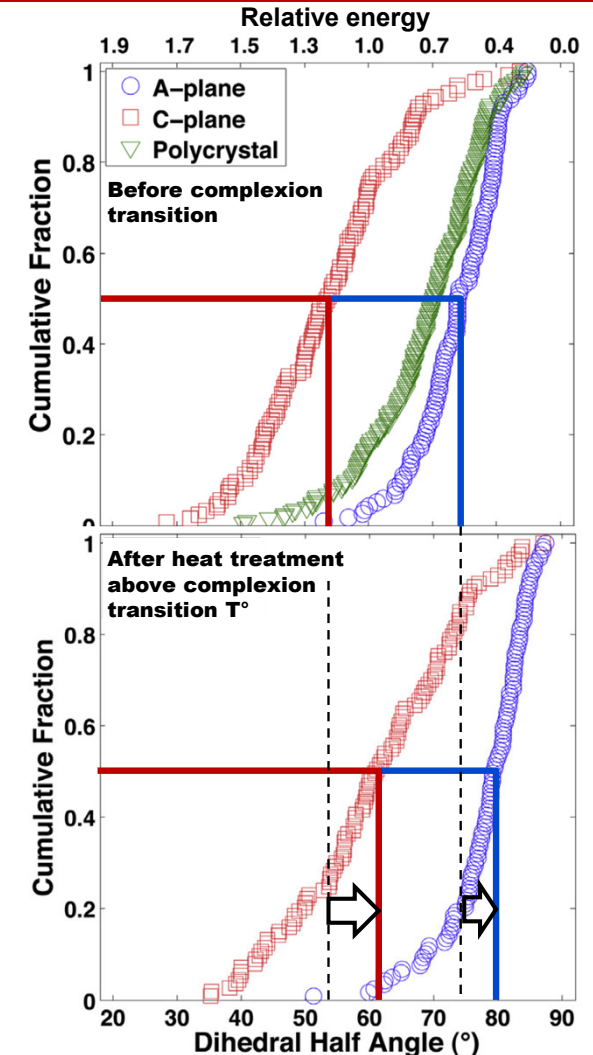
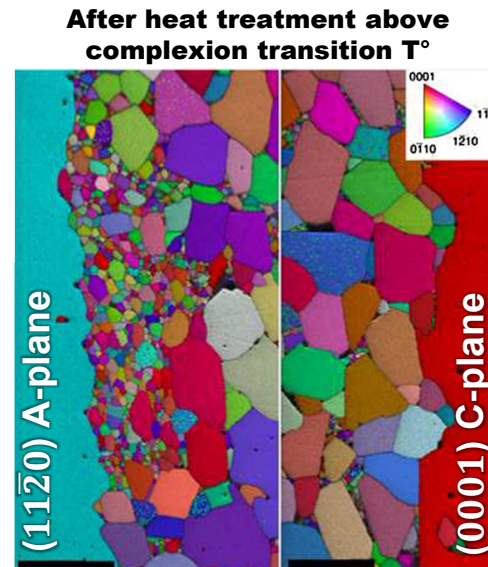
Complexion effects

Effect of grain boundary energy on complexion transitions

Example of Y-doped alumina

- ◆ After complexion transition average grain boundary energy decreases at both interfaces but ranges appear to remain significantly similar. Two explanations:
 - ➔ High energy GBs form during grain growth
 - ➔ Complexion transitions occur by nucleation-growth
- ◆ Significantly larger grains at C-planes which can be due to:
 - Complexion transitions occurring at lower T°
 - Complexion transitions have lower nucleation energy barrier
- ◆ Interface moved further into the single crystal in C-plane compared to A-plane
 - ➔ mobility or growth time difference

Complexion transitions more likely to occur at high energy GBs

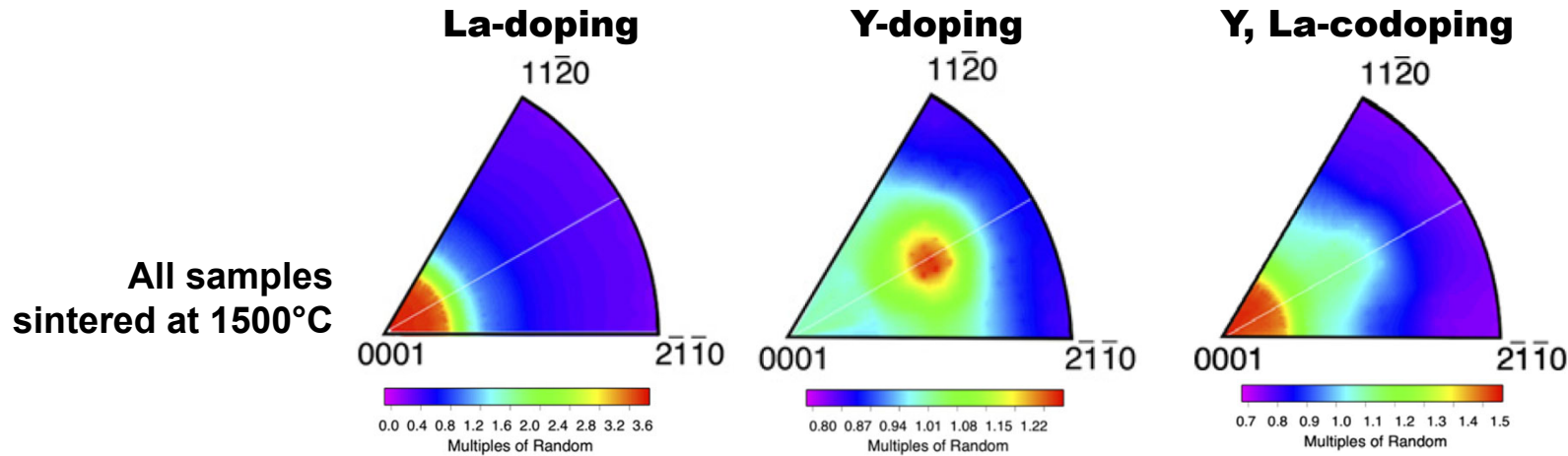


Complexion effects

Effect of co-doping on GBPD

Example of Y- and La-codoped alumina

- ♦ Co-doping may (not a rule) allow combining effects on GBPD from single-doping



- ♦ Y-/La-codoping shows a preference for $\{0001\}$ and $\{1\bar{1}02\}$ oriented grain boundaries, whereby
La-doping has a preference for $\{0001\}$ and
Y-doping (at this temperature = transient) has a preference for $\{1\bar{1}02\}$

Final remarks

- ◆ Grain boundary engineering including complexions and complexion transitions is a new approach in advanced microstructure engineering
- ◆ It is not excluded that complexion transitions occur without affecting GB mobility but leading to other discontinuous property changes
- ◆ How to control grain boundary population and complexions in real systems
 - Particle crystal orientation alignment
 - ➔ use of anisometric particles (e.g. shear),
 - ➔ use of external forces during colloidal processing with anisotropic particles (e.g. magnetic alignment)
 - Use of adapted particle size to allow reaching target grain size after complexion transition induced grain growth
 - Use of dopants and dopant mixtures, including doping levels (i.e. complexion transitions typically involve chemical (dopant adsorption to GB) changes)
 - Trigger/avoid complexion transitions during densification by using rapid sintering techniques
 - Use of pressure or other external forces (i.e. complexion transitions obey thermodynamic laws)

The end

What was on the
- MENU -
today ?



◆ Summary

- Complexion and complexion transitions in grain boundaries
- Type of complexion transitions and (non-)congruency thereof
- Basics about EBSD
- Stereological EBSD analysis to determine GBPD and GBPD
- Effects of complexion transition on GBPD and GBPD towards advanced grain boundary engineering

◆ Questions